Ref #	Hits	Search Query	DBs	Default Operat or	Plural s	Time Stamp
L34	267	bond\$3 with chip with metal with (powder or particle)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:11
L36	144	bond\$3 adj (chip or substrate or carrier or electronic or semiconductor) near5 metal near5 (powder or particle)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:12
L37	36	bond\$3 adj (chip or substrate or carrier or electronic or semiconductor) near5 metal adj (powder or particle)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:13
L38	864	228/193.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:32
L41	492	228/194.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:34

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L43	389	228/245.ccls.	US-PGPU B; USPAT; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:35		
L44	479	228/246.ccls.	US-PGPU B; USPAT; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:35		
L45	577	228/248.1.ccls.	US-PGPU B; USPAT; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:36		
L46	68	228/248.5.ccls.	US-PGPU B; USPAT; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:36		
L48	588	228/234.1.ccls.	US-PGPU B; USPAT; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:36		
L49	83	219/129.ccls.	US-PGPU B; USPAT; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:48		

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L50	3158	38 or 41 or 42 or 43 or 44 or 45 or 46 or 48 or 49	US-PGPU B; USPAT; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:49
L52	2	10 and bond\$3 and position\$3 and (member or component) with (plat\$3 or electrodeposit or electroplat\$3)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:51
L53	7	10 and bond\$3 and position\$3 and (member or component) and (plat\$3 or electrodeposit or electroplat\$3)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:52
L54	9	10 and (bond\$3 or join\$3) and position\$3 and (member or component) and (plat\$3 or electrodeposit or electroplat\$3)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:52
L55	2	10 and (bond\$3 or join\$3) and position\$3 and (member or component) and (plat\$3 or electrodeposit or electroplat\$3)and (particle or powder)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:53

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L56	3	10 and (bond\$3 or join\$3) and (member or component) and (plat\$3 or electrodeposit or electroplat\$3)and (particle or powder)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:53
L57	4	10 and (bond\$3 or join\$3) and (member or component) and (particle or powder)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 17:53
L61	2	10 and (bond\$3 or join\$3) and (member or component) and (semiconductor or chip or carrier or substrate or electronic or optical) same (particle or powder)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 18:00
L63	244	(bond\$3 or join\$3) near5 (member or component) near5 (semiconductor or chip or carrier or substrate or electronic or optical) near5 (particle or powder)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/04/21 18:01

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